

V_{DSS}	20V
$R_{DS(on)}$ (Max.)	105mΩ
I_D	2A
P_D	1W

●Features

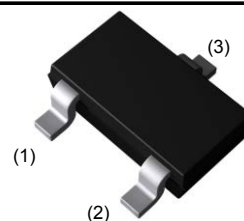
- 1) Low on - resistance.
- 2) Built-in G-S Protection Diode.
- 3) Small Surface Mount Package (TSMT3).
- 4) Pb-free lead plating ; RoHS compliant

●Application

Road SW

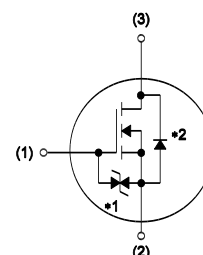
●Outline

TSMT3



●Inner circuit

- (1) Gate
- (2) Source
- (3) Drain



*1 ESD PROTECTION DIODE

*2 BODY DIODE

●Packaging specifications

Type	Packaging	Taping
	Reel size (mm)	180
	Tape width (mm)	8
	Basic ordering unit (pcs)	3,000
	Taping code	TL
	Marking	XK

●Absolute maximum ratings($T_a = 25^\circ\text{C}$)

Parameter	Symbol	Value	Unit
Drain - Source voltage	V_{DSS}	20	V
Continuous drain current	I_D^{*1}	±2	A
Pulsed drain current	$I_{D,pulse}^{*2}$	±6	A
Gate - Source voltage	V_{GSS}	±10	V
Power dissipation	P_D^{*3}	1.0	W
	P_D^{*4}	0.54	W
Junction temperature	T_j	150	°C
Range of storage temperature	T_{stg}	-55 to +150	°C

●Thermal resistance

Parameter	Symbol	Values			Unit
		Min.	Typ.	Max.	
Thermal resistance, junction - ambient	R_{thJA}^{*3}	-	-	125	°C/W
Thermal resistance, junction - ambient	R_{thJA}^{*4}	-	-	231	°C/W

●Electrical characteristics($T_a = 25^\circ\text{C}$)

Parameter	Symbol	Conditions	Values			Unit
			Min.	Typ.	Max.	
Drain - Source breakdown voltage	$V_{(BR)DSS}$	$V_{GS} = 0V, I_D = 1mA$	20	-	-	V
Breakdown voltage temperature coefficient	$\frac{\Delta V_{(BR)DSS}}{\Delta T_j}$	$I_D = 1mA$ referenced to 25°C	-	20	-	mV/°C
Zero gate voltage drain current	I_{DSS}	$V_{DS} = 20V, V_{GS} = 0V$	-	-	1	μA
Gate - Source leakage current	I_{GSS}	$V_{GS} = \pm 10V, V_{DS} = 0V$	-	-	±10	μA
Gate threshold voltage	$V_{GS(th)}$	$V_{DS} = 10V, I_D = 1mA$	0.3	-	1.0	V
Gate threshold voltage temperature coefficient	$\frac{\Delta V_{(GS)th}}{\Delta T_j}$	$I_D = 1mA$ referenced to 25°C	-	-1.9	-	mV/°C
Static drain - source on - state resistance	$R_{DS(on)}^{*5}$	$V_{GS}=4.5V, I_D=2A$	-	75	105	mΩ
		$V_{GS}=2.5V, I_D=2A$	-	95	135	
		$V_{GS}=1.8V, I_D=1A$	-	130	185	
		$V_{GS}=1.5V, I_D=0.4A$	-	170	240	
		$V_{GS}=4.5V, I_D=2A, T_j=125^\circ\text{C}$	-	120	170	
Gate input resistance	R_G	$f = 1MHz, \text{open drain}$	-	24	-	Ω
Transconductance	g_{fs}^{*5}	$V_{DS} = 10V, I_D = 2A$	1.8	4.2	-	S

*1 Limited only by maximum temperature allowed.

*2 $P_w \leq 10\mu s$, Duty cycle $\leq 1\%$

*3 Mounted on a ceramic board (30×30×0.8mm)

*4 Mounted on a FR4 (12×20×0.8mm)

●Electrical characteristics($T_a = 25^\circ\text{C}$)

Parameter	Symbol	Conditions	Values			Unit
			Min.	Typ.	Max.	
Input capacitance	C_{iss}	$V_{GS} = 0V$	-	180	-	pF
Output capacitance	C_{oss}	$V_{DS} = 10V$	-	45	-	
Reverse transfer capacitance	C_{rss}	$f = 1\text{MHz}$	-	25	-	
Turn - on delay time	$t_{d(on)}^{*5}$	$V_{DD} \approx 10V, V_{GS} = 4.5V$	-	6	-	ns
Rise time	t_r^{*5}	$I_D = 1A$	-	17	-	
Turn - off delay time	$t_{d(off)}^{*5}$	$R_L = 10\Omega$	-	30	-	
Fall time	t_f^{*5}	$R_G = 10\Omega$	-	30	-	

●Gate Charge characteristics($T_a = 25^\circ\text{C}$)

Parameter	Symbol	Conditions	Values			Unit
			Min.	Typ.	Max.	
Total gate charge	Q_g^{*5}	$V_{DD} \approx 10V, I_D = 2A$ $V_{GS} = 4.5V$	-	2.0	-	nC
Gate - Source charge	Q_{gs}^{*5}	$V_{DD} \approx 10V, I_D = 2A$	-	0.6	-	
Gate - Drain charge	Q_{gd}^{*5}	$V_{GS} = 4.5V$	-	0.4	-	

●Body diode electrical characteristics (Source-Drain)($T_a = 25^\circ\text{C}$)

Parameter	Symbol	Conditions	Values			Unit
			Min.	Typ.	Max.	
Inverse diode continuous, forward current	I_s^{*1}	$T_a = 25^\circ\text{C}$	-	-	0.8	A
Forward voltage	V_{SD}^{*5}	$V_{GS} = 0V, I_s = 2A$	-	-	1.2	V

*5 Pulsed

●Electrical characteristic curves

Fig.1 Power Dissipation Derating Curve

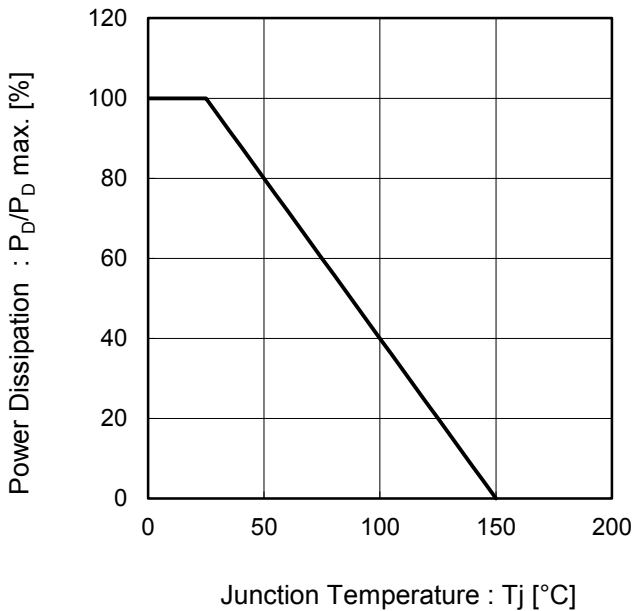


Fig.2 Maximum Safe Operating Area

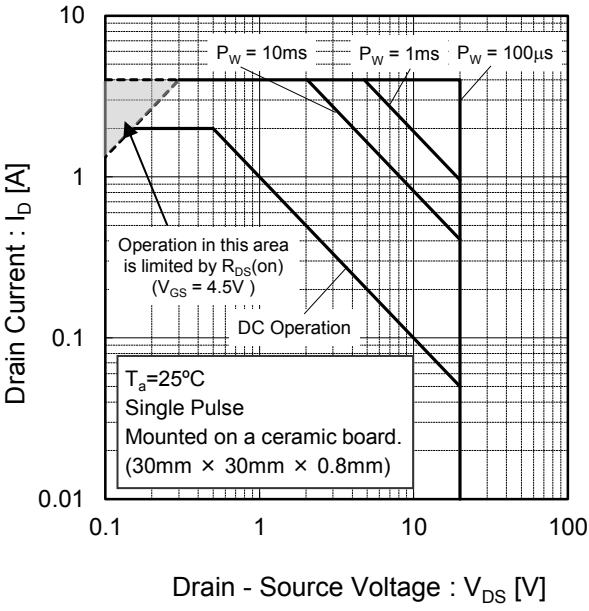


Fig.3 Normalized Transient Thermal Resistance vs. Pulse Width

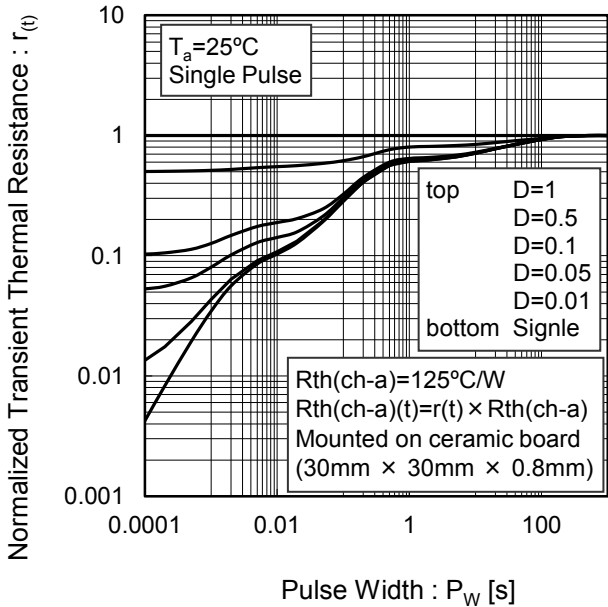
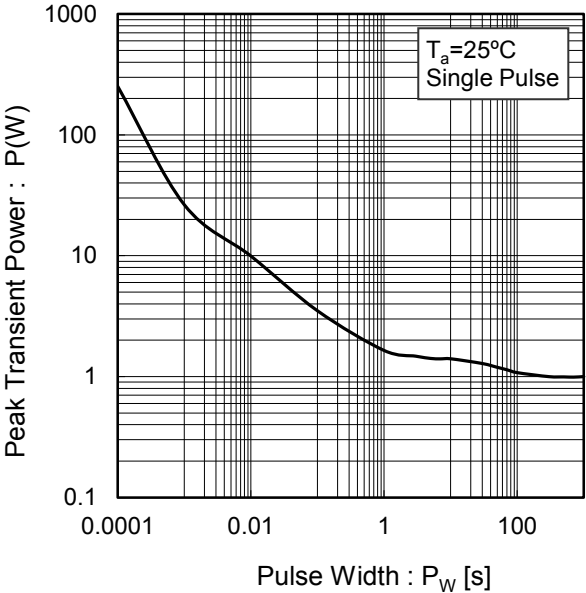


Fig.4 Single Pulse Maximum Power dissipation



●Electrical characteristic curves

Fig.5 Typical Output Characteristics(I)

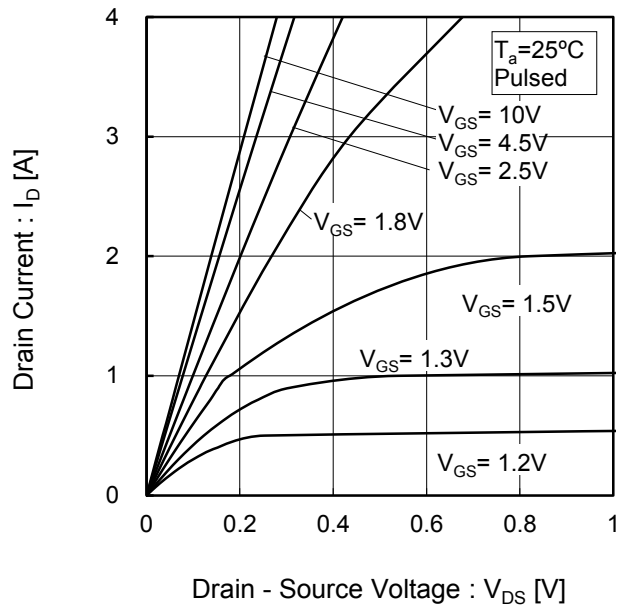
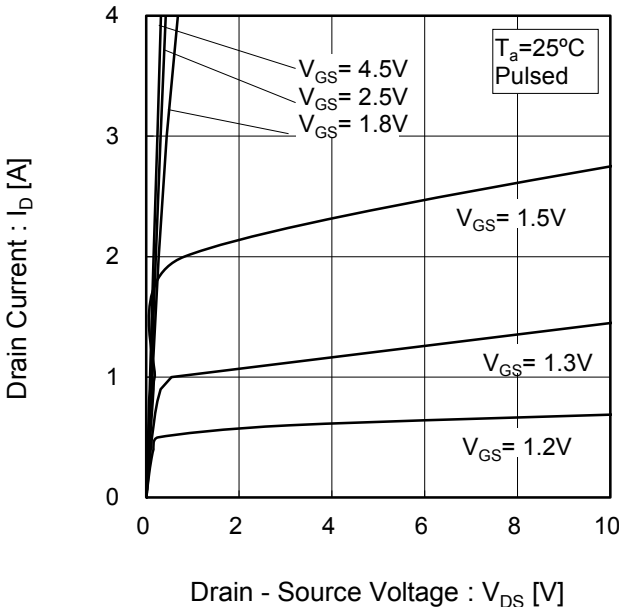
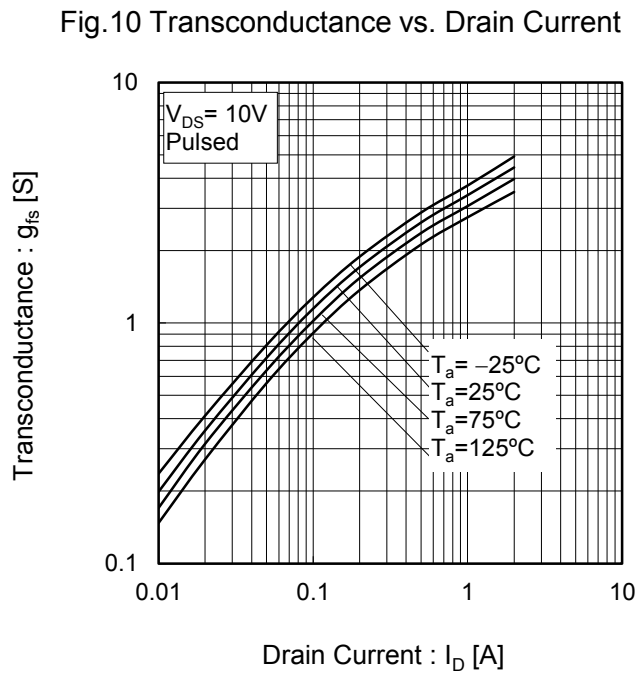
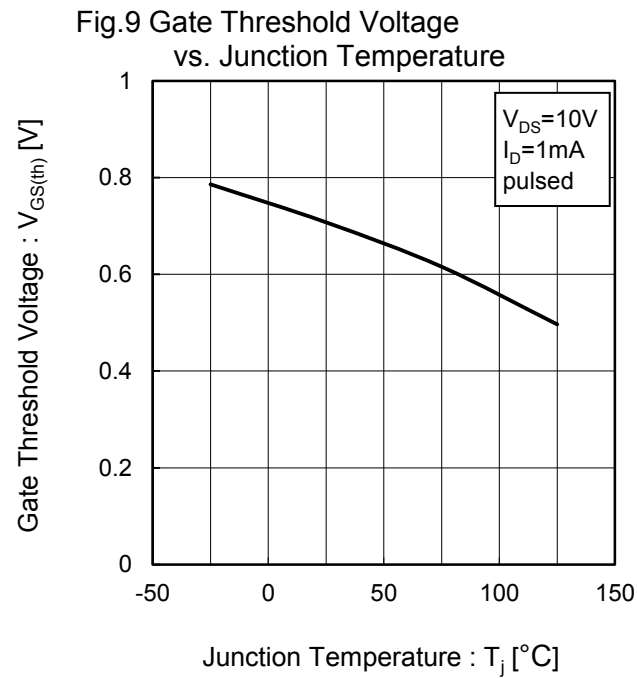
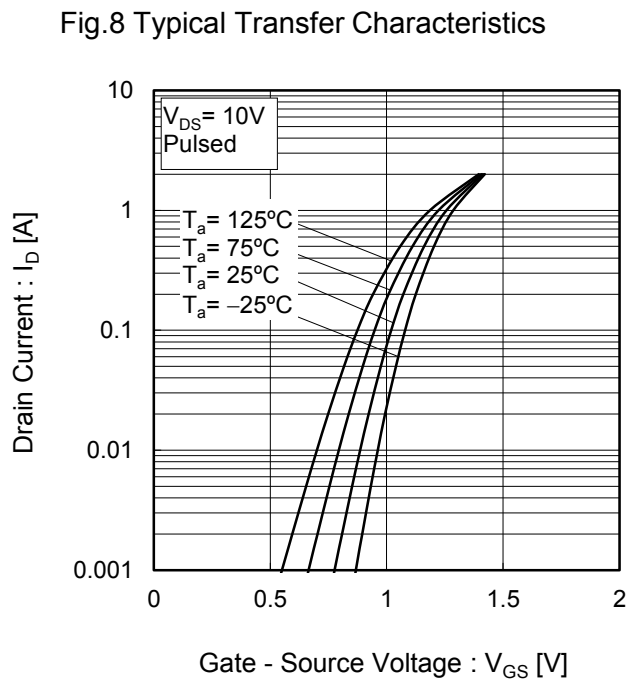
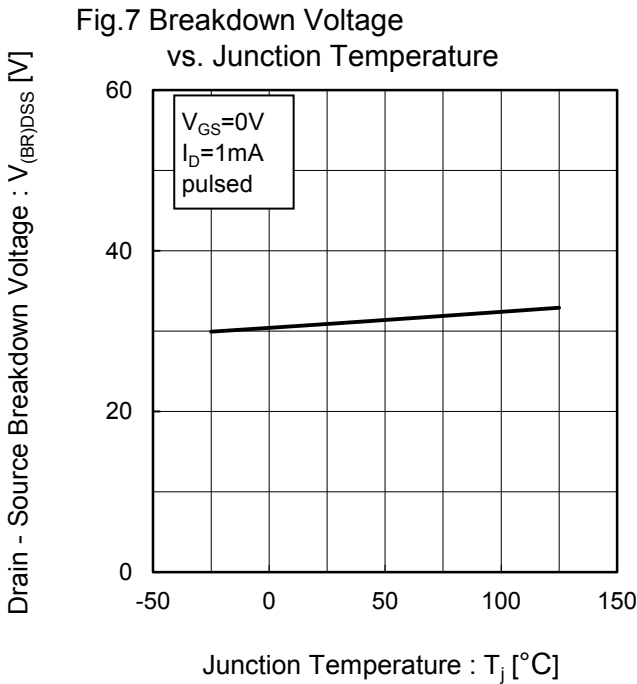


Fig.6 Typical Output Characteristics(II)



●Electrical characteristic curves



●Electrical characteristic curves

Fig.11 Drain CurrentDerating Curve

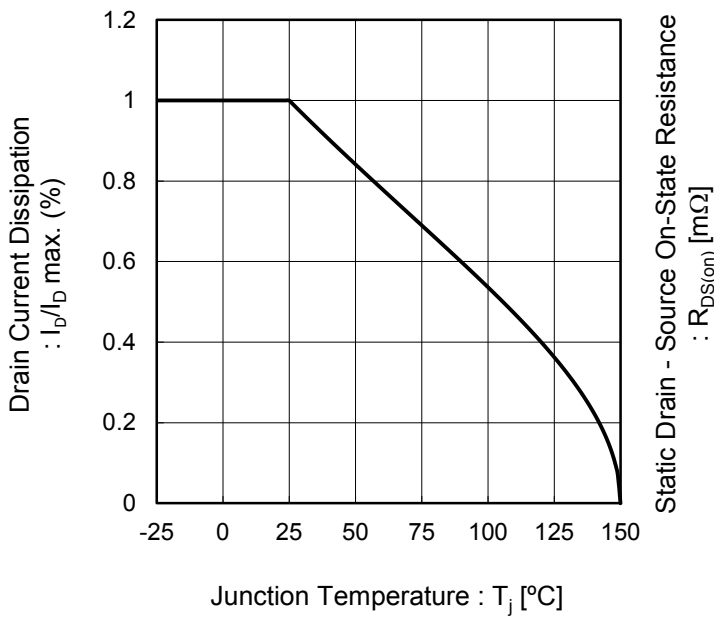


Fig.12 Static Drain - Source On - State Resistance vs. Gate Source Voltage

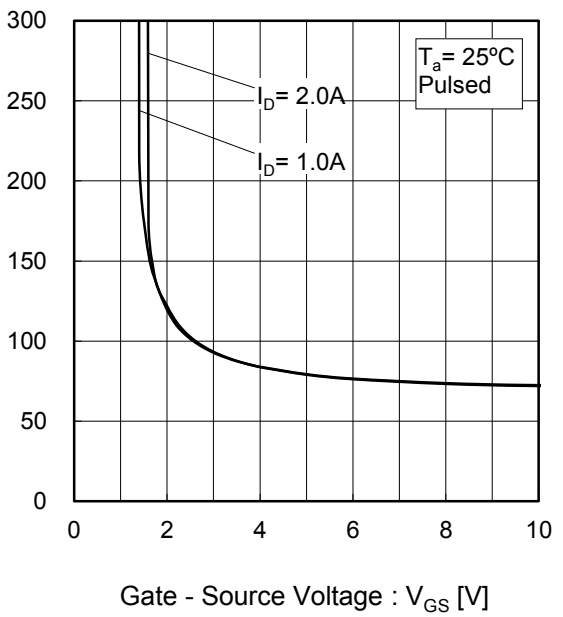


Fig.13 Static Drain - Source On - State Resistance vs. Drain Current(I)

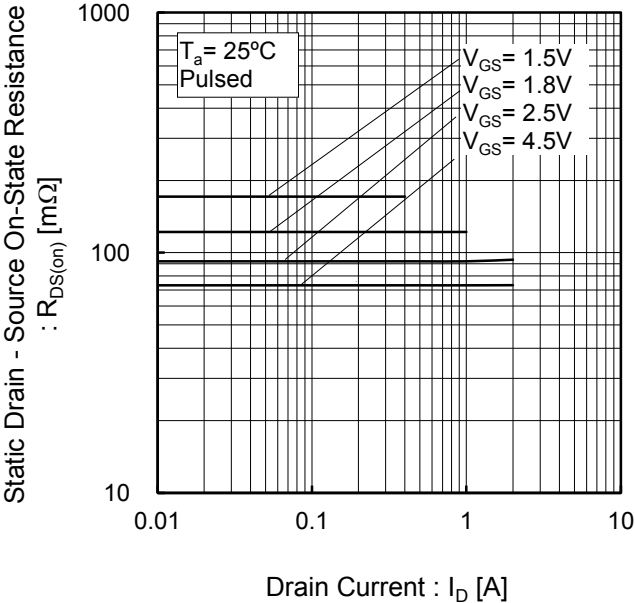
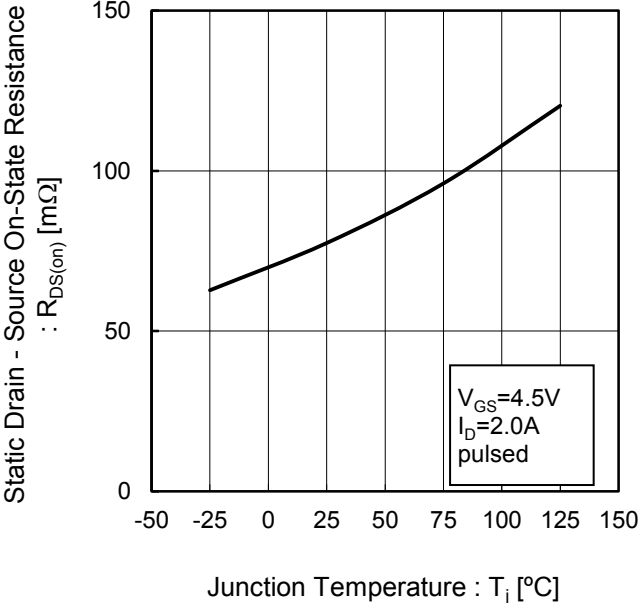


Fig.14 Static Drain - Source On - State Resistance vs. Junction Temperature



●Electrical characteristic curves

Fig.15 Static Drain-Source On-State Resistance vs. Drain Current(II)

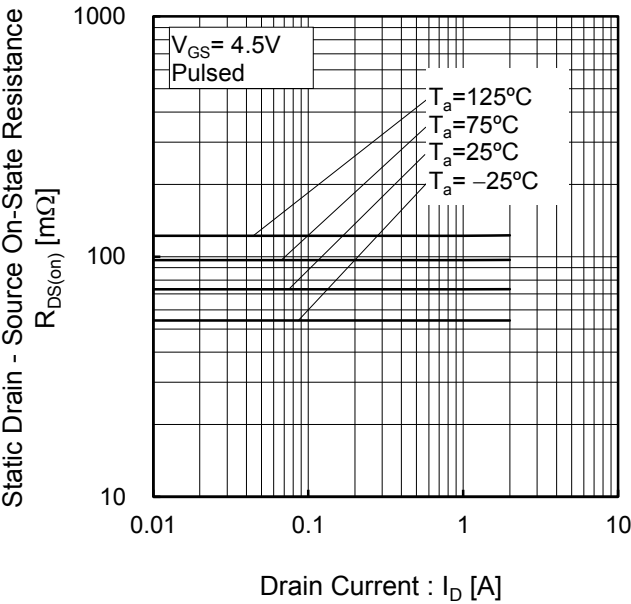


Fig.16 Static Drain - Source On - State Resistance vs. Drain Current(III)

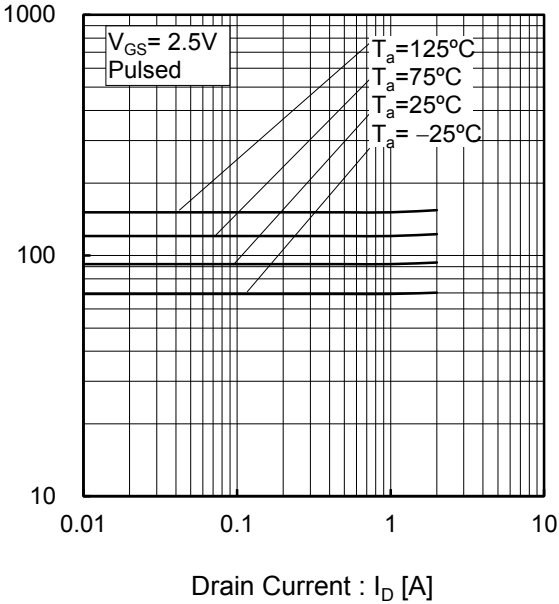
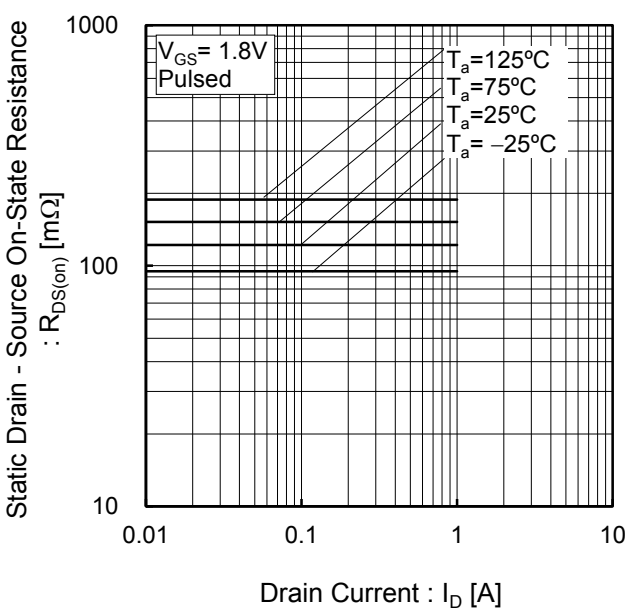


Fig.17 Static Drain - Source On - State Resistance vs. Drain Current(IV)



●Electrical characteristic curves

Fig.18 Typical Capacitance vs. Drain - Source Voltage

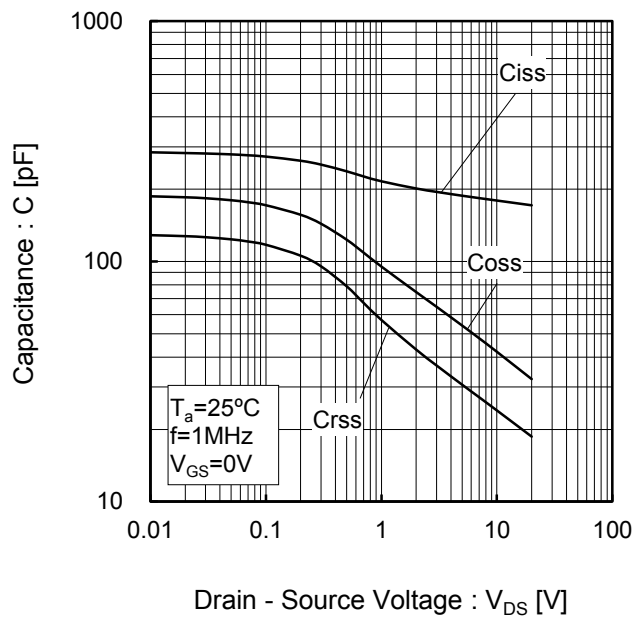


Fig.19 Switching Characteristics

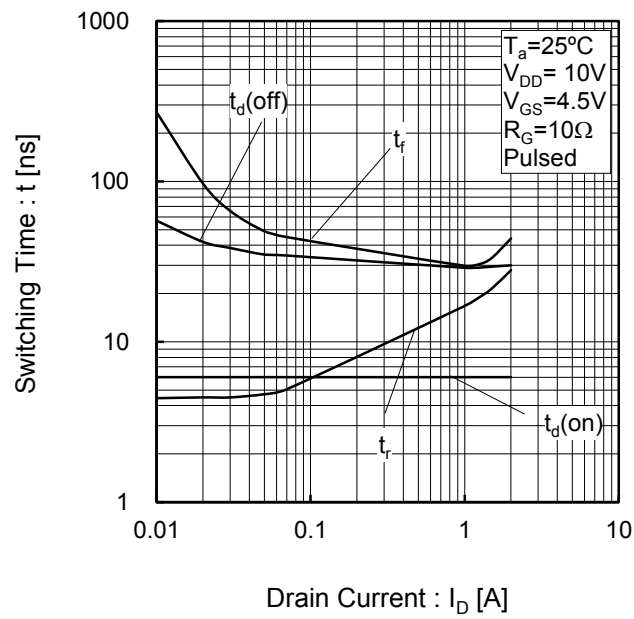


Fig.20 Dynamic Input Characteristics

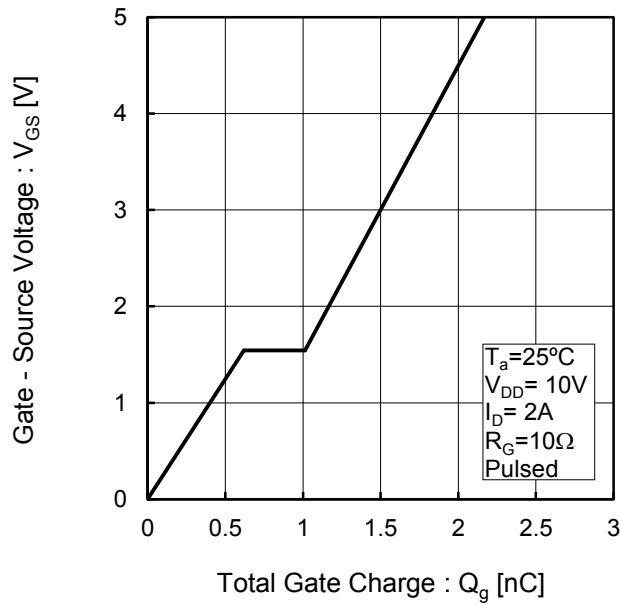
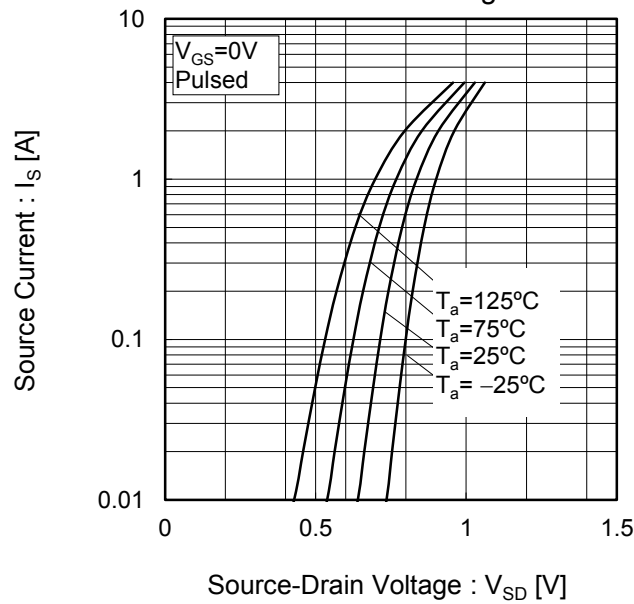


Fig.21 Source Current vs. Source Drain Voltage



●Measurement circuits

Fig.1-1 Switching Time Measurement Circuit

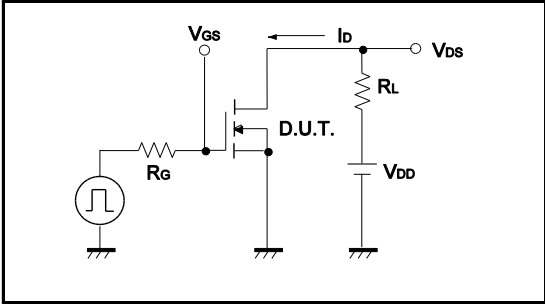


Fig.1-2 Switching Waveforms

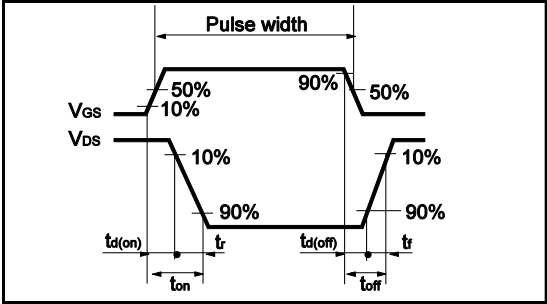


Fig.2-1 Gate Charge Measurement Circuit

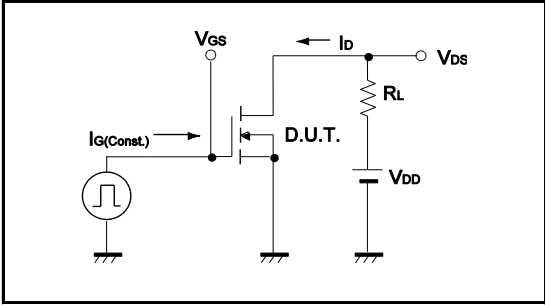
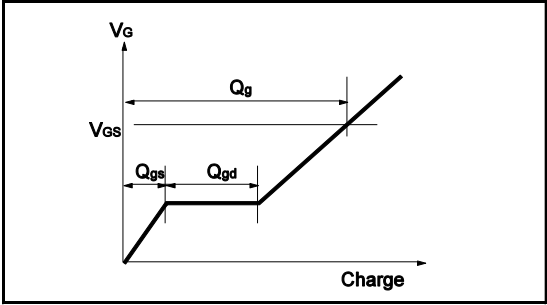
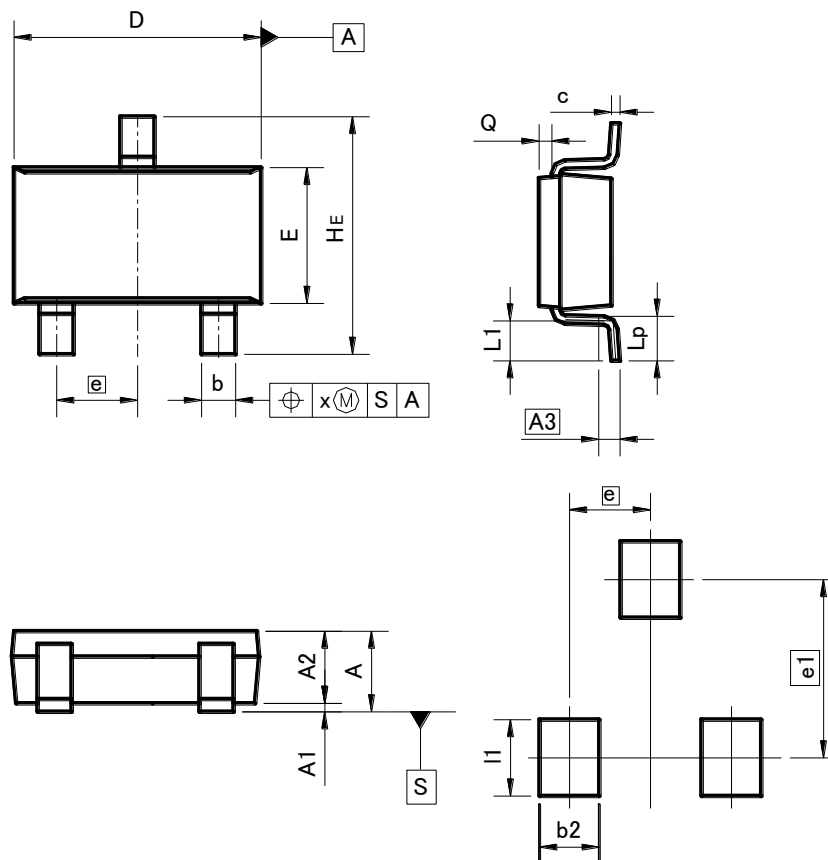


Fig.2-2 Gate Charge Waveform



●Dimensions (Unit : mm)

TSMT3



Pattern of terminal position areas

DIM	MILIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	—	1.00	—	0.039
A1	0.00	0.10	0	0.004
A2	0.75	0.95	0.03	0.037
A3	0.25		0.01	
b	0.35	0.50	0.014	0.02
c	0.10	0.26	0.004	0.01
D	2.80	3.00	0.11	0.118
E	1.50	1.80	0.059	0.071
e	0.95		0.04	
HE	2.60	3.00	0.102	0.118
L1	0.30	0.60	0.012	0.024
Lp	0.40	0.70	0.016	0.028
Q	0.05	0.25	0.002	0.01
x	—	0.20	—	0.008

DIM	MILIMETERS		INCHES	
	MIN	MAX	MIN	MAX
e1	2.10		0.08	
b2	—	0.70	—	0.028
l1	—	0.90	—	0.035

Dimension in mm/inches

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